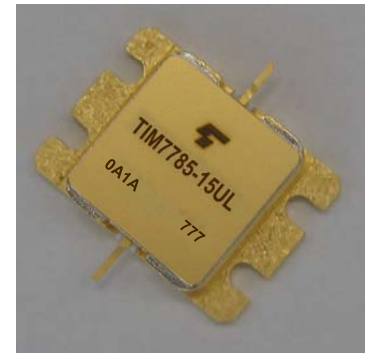


### FEATURES

- BROAD BAND INTERNALLY MATCHED FET
- HIGH POWER  
P1dB= 42.0dBm at 7.7GHz to 8.5GHz
- HIGH GAIN  
G1dB= 8.5dB at 7.7GHz to 8.5GHz
- LOW INTERMODULATION DISTORTION  
IM3= -47dBc at Pout=31.0dBm  
Single Carrier Level
- HERMETICALLY SEALED PACKAGE



### RF PERFORMANCE SPECIFICATIONS ( Ta= 25°C )

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain Compression Point	P1dB	VDS= 10V IDSset= 3.2A f = 7.7 to 8.5GHz	dBm	41.0	42.0	—
Power Gain at 1dB Gain Compression Point	G1dB		dB	7.5	8.5	—
Drain Current	IDS1		A	—	3.5	4.0
Gain Flatness	ΔG		dB	—	—	±0.6
Power Added Efficiency	ηadd		%	—	39	—
3rd Order Intermodulation Distortion	IM3	Two Tone Test Po= 31.0dBm, Δf= 5MHz (Single Carrier Level)	dBc	-42	-47	—
Drain Current	IDS2		A	—	3.5	4.0
Channel Temperature Rise	ΔTch	(VDS X IDS + Pin – P1dB) X Rth(c-c)	°C	—	—	80

**Recommended Gate Resistance(Rg): 68 Ω**

### ELECTRICAL CHARACTERISTICS ( Ta= 25°C )

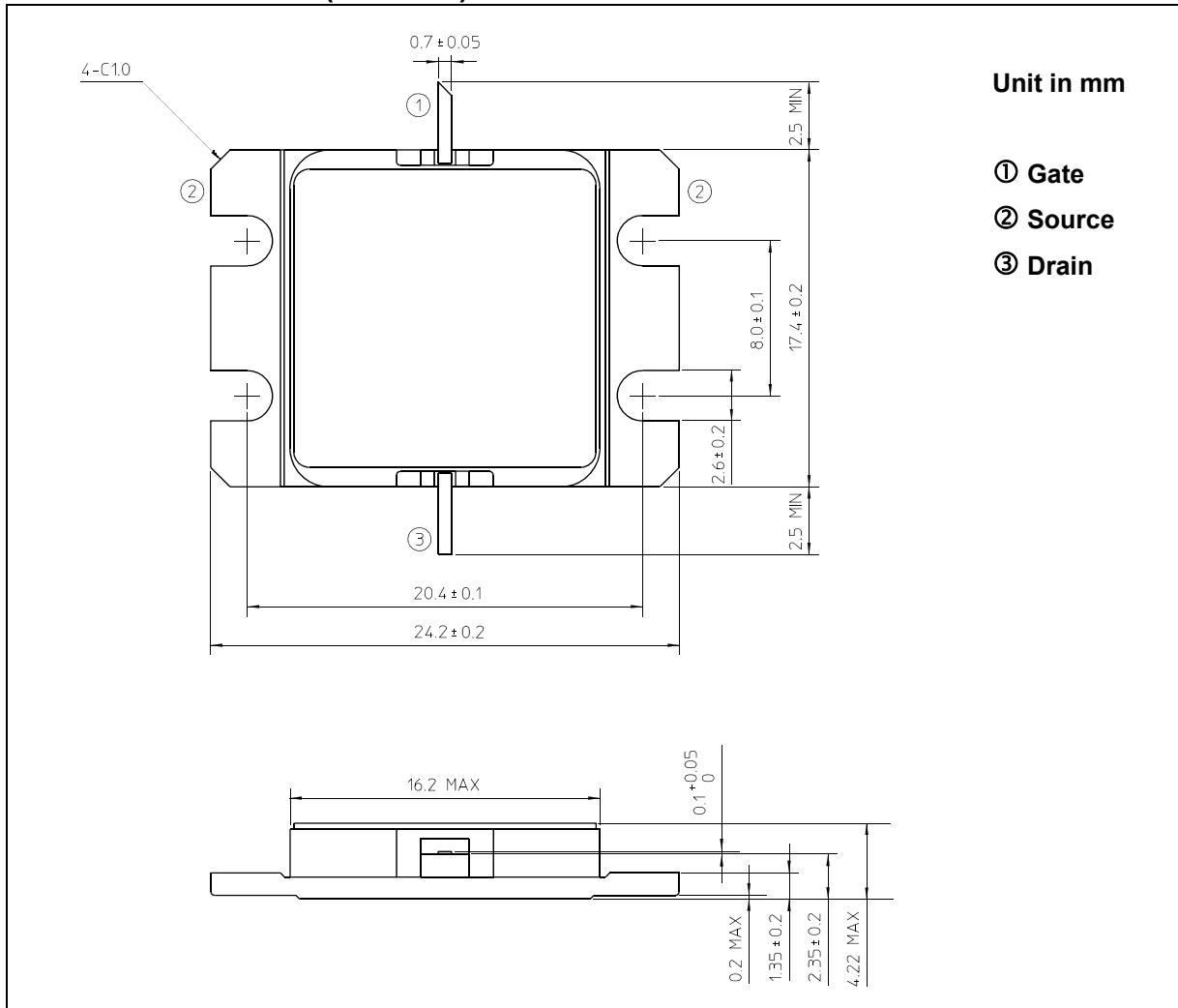
CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 5.0A	S	—	4.0	—
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 40mA	V	-0.5	-2.0	-3.0
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	A	—	8.0	—
Gate-Source Breakdown Voltage	VGSO	IGS= -120μA	V	-5	—	—
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W	—	2.0	2.4

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**ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)**

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	A	12.0
Total Power Dissipation (Tc= 25 °C)	PT	W	62.5
Channel Temperature	Tch	°C	175
Storage Temperature	Tstg	°C	-65 to +175

**PACKAGE OUTLINE (2-16G1B)**

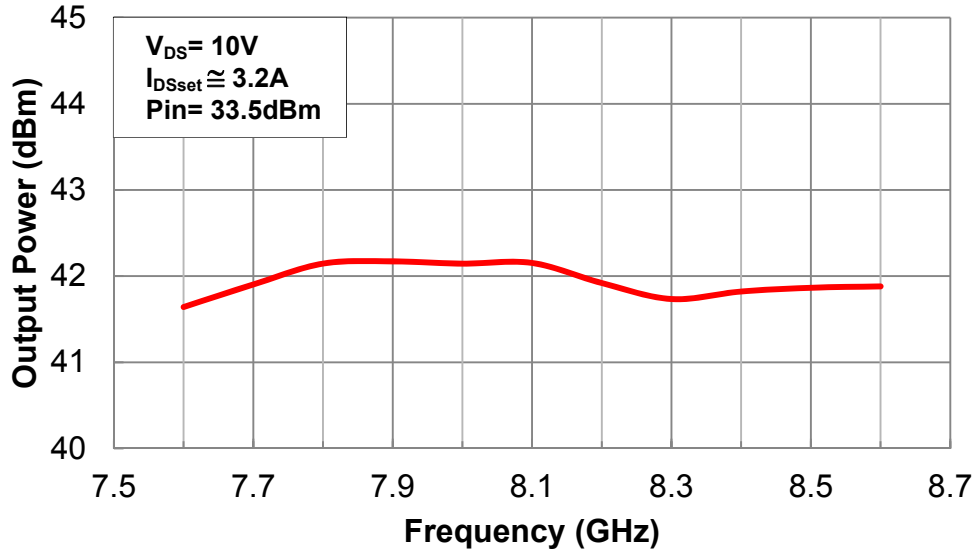


**HANDLING PRECAUTIONS FOR PACKAGE MODEL**

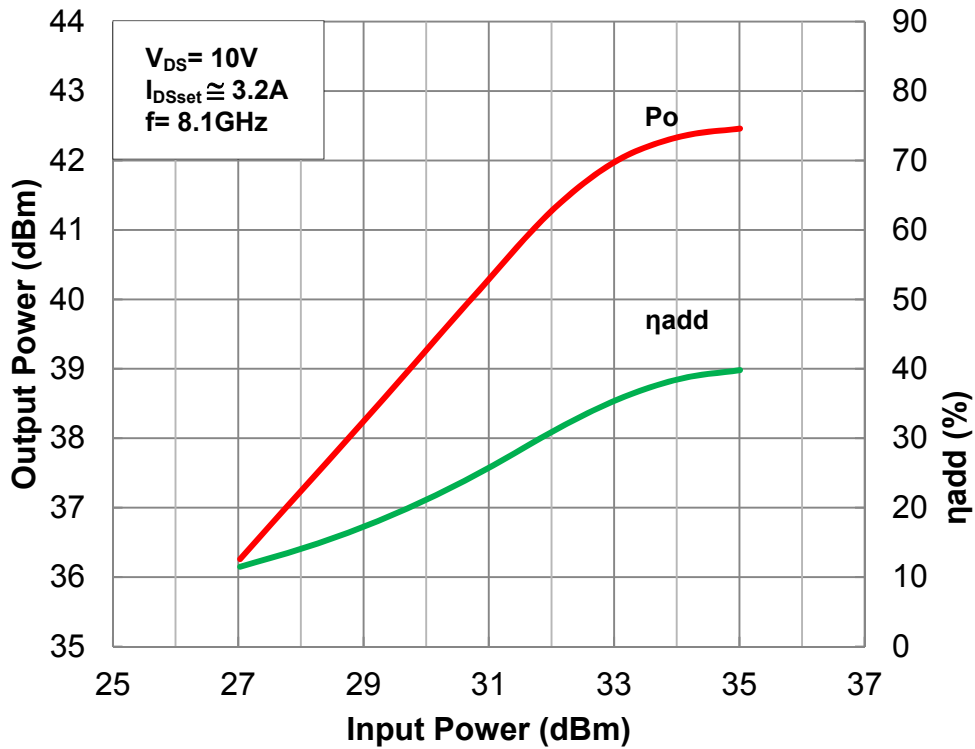
Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.

**RF PERFORMANCE**

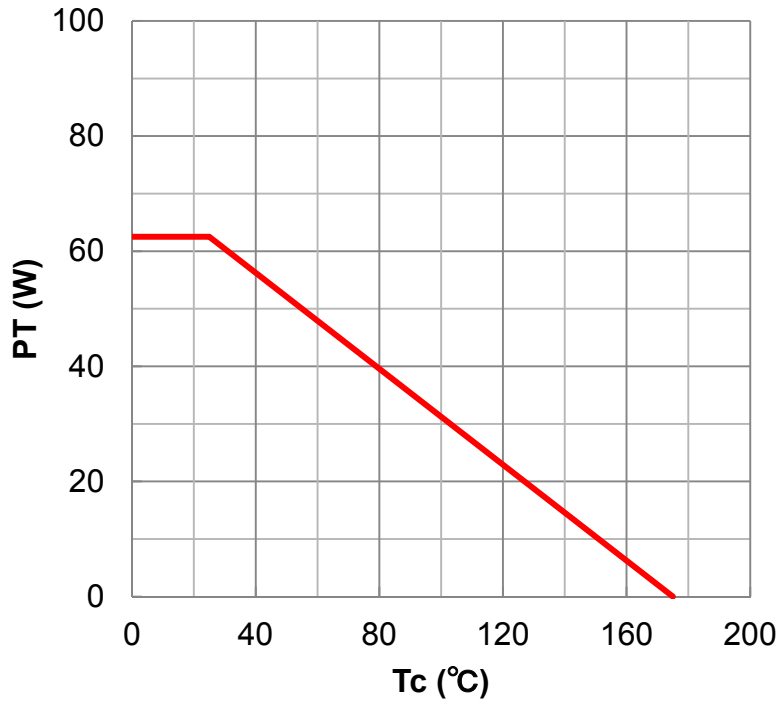
**Output Power vs. Frequency**



**Output Power vs. Input Power**



**Power Dissipation vs. Case Temperature**



**IM3 vs. Output Power Characteristics**

